
CSE477

VLSI Digital Circuits

Fall 2002

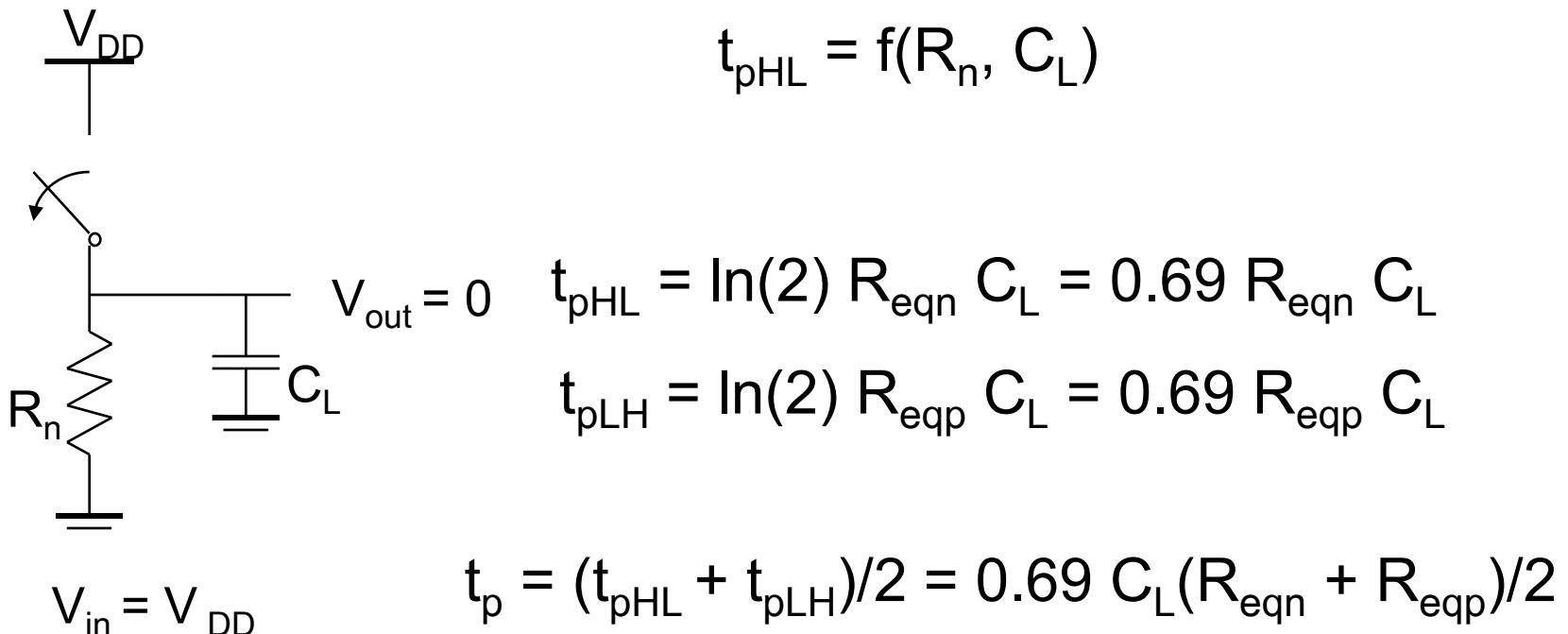
Lecture 10: The Inverter, A Dynamic View

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[Adapted from Rabaey's *Digital Integrated Circuits*, ©2002, J. Rabaey et al.]

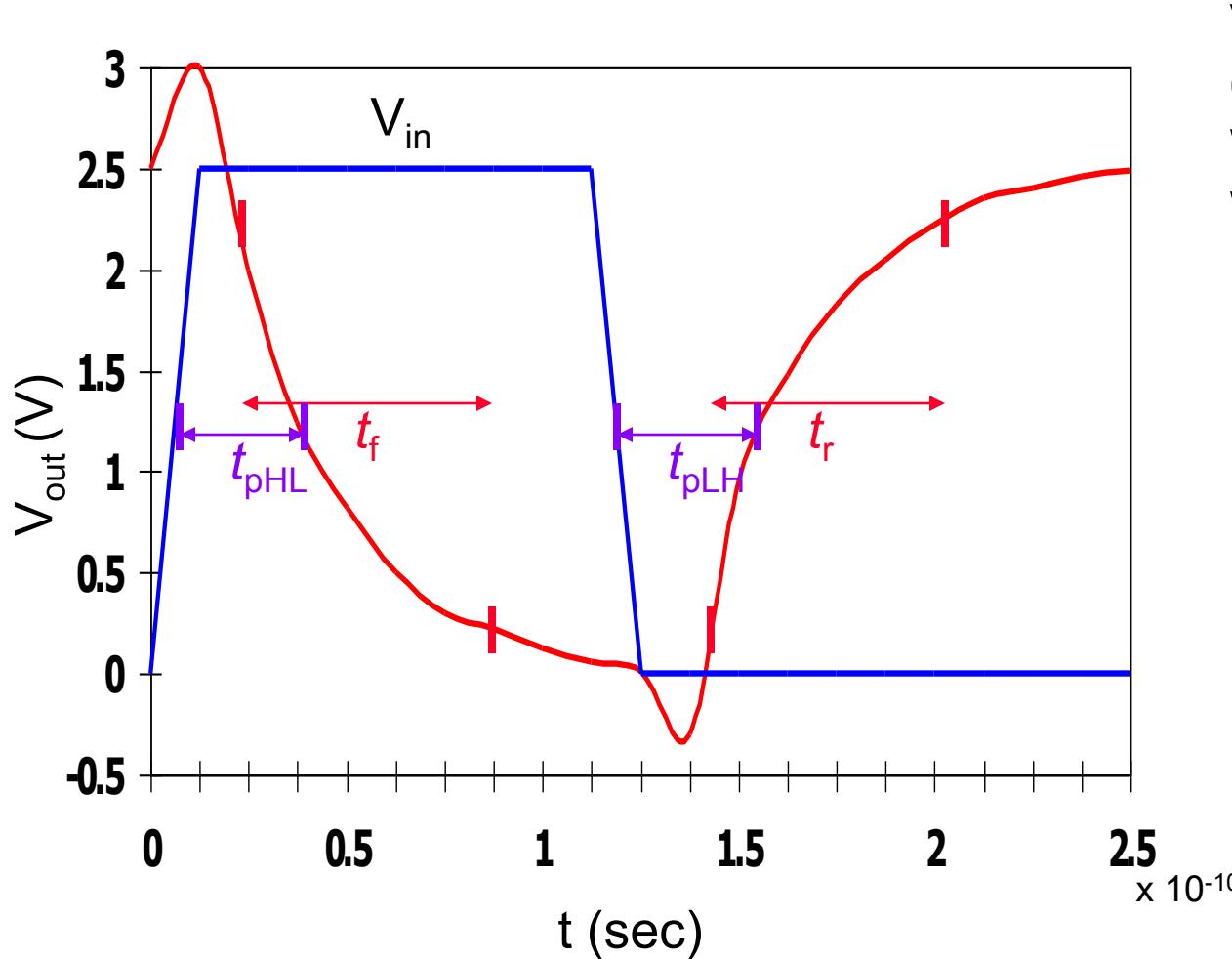
Inverter Propagation Delay

- Propagation delay is proportional to the time-constant of the network formed by the pull-down resistor and the load capacitance



- To equalize rise and fall times make the on-resistance of the NMOS and PMOS approximately equal.

Inverter Transient Response



$V_{DD} = 2.5V$
 $0.25\mu m$
 $W/L_n = 1.5$
 $W/L_p = 4.5$
 $R_{eqn} = 13 k\Omega (\div 1.5)$
 $R_{eqp} = 31 k\Omega (\div 4.5)$

$$t_{pHL} = 36 \text{ psec}$$

$$t_{pLH} = 29 \text{ psec}$$

so

$$t_p = 32.5 \text{ psec}$$

From simulation: $t_{pHL} = 39.9 \text{ psec}$ and $t_{pLH} = 31.7 \text{ psec}$

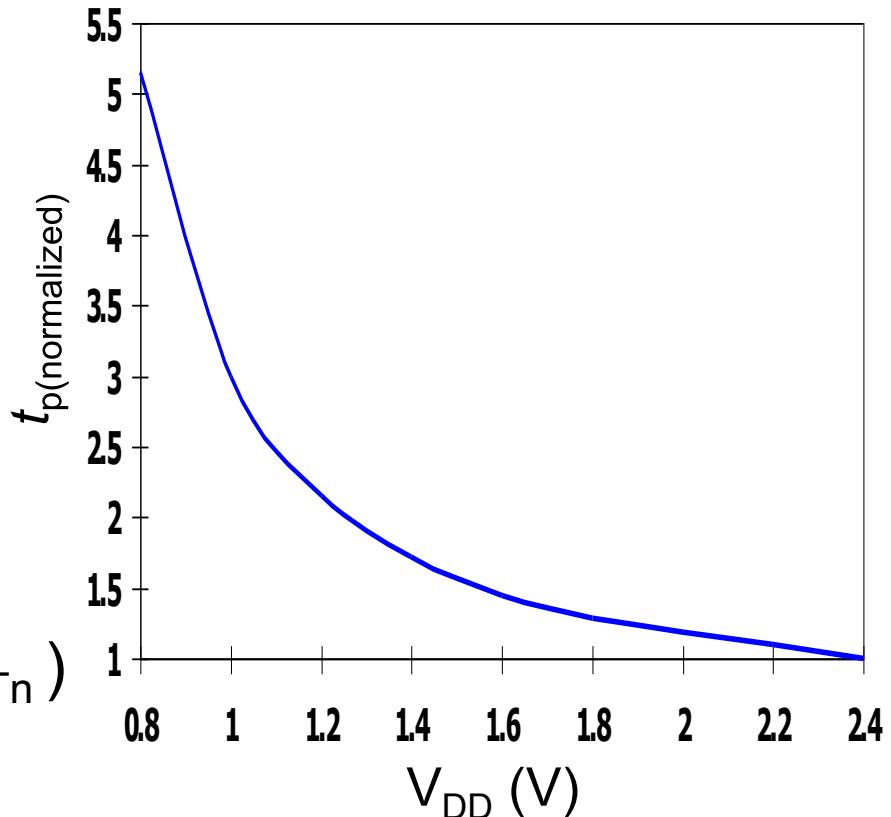
Inverter Propagation Delay, Revisited

- To see how a **designer** can optimize the delay of a gate have to expand the R_{eq} in the delay equation

$$t_{pHL} = 0.69 R_{eqn} C_L$$

$$= 0.69 \left(\frac{3}{4} \left(C_L V_{DD} \right) / I_{DSATn} \right)$$

$$\approx 0.52 C_L / (W/L_n k'_n V_{DSATn})$$



Design for Performance

- Reduce C_L
 - internal diffusion capacitance of the gate itself
 - keep the drain diffusion as small as possible
 - interconnect capacitance
 - fanout
- Increase W/L ratio of the transistor
 - the most powerful and effective performance optimization tool in the hands of the designer
 - watch out for **self-loading!** – when the intrinsic capacitance dominates the extrinsic load
- Increase V_{DD}
 - can trade-off energy for performance
 - increasing V_{DD} above a certain level yields only very minimal improvements
 - reliability concerns enforce a firm upper bound on V_{DD}

NMOS/PMOS Ratio

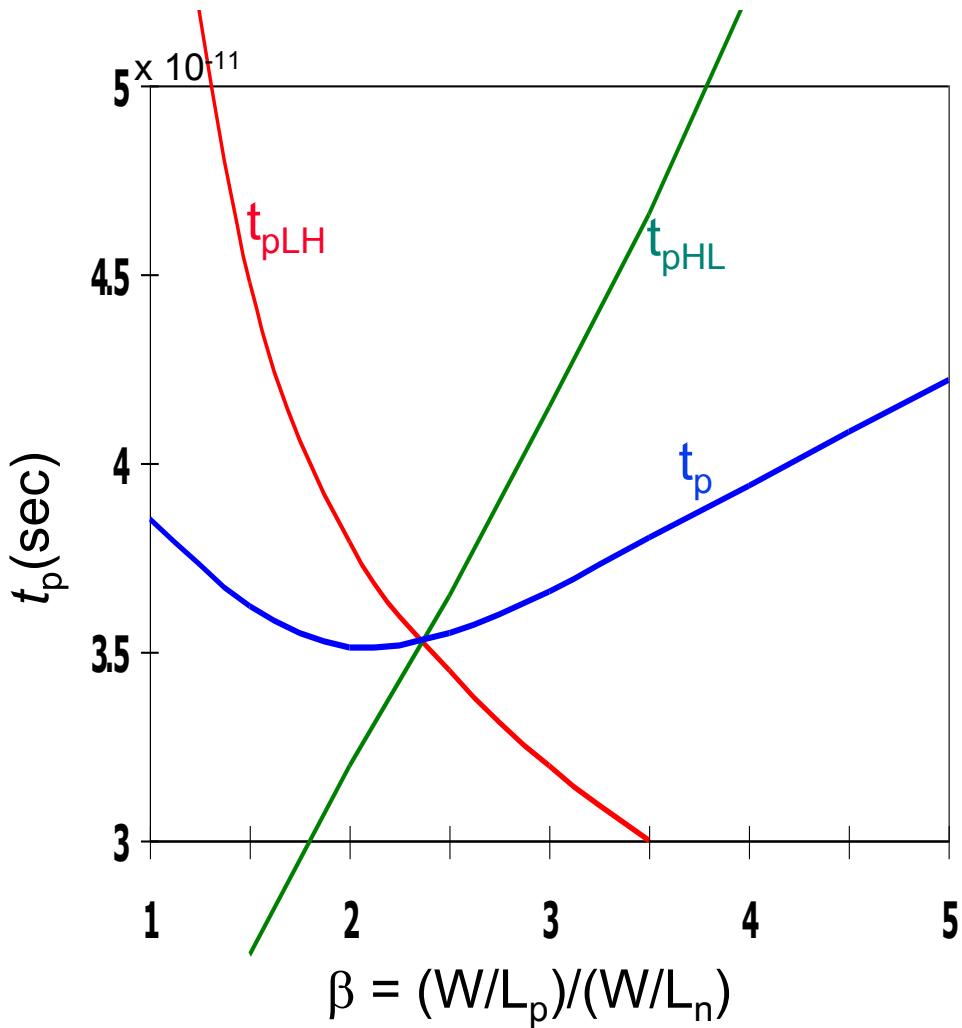
- ❑ So far have sized the PMOS and NMOS so that the R_{eq} 's match (ratio of 3 to 3.5)
 - ❑ symmetrical VTC
 - ❑ equal high-to-low and low-to-high propagation delays
- ❑ If speed is the only concern, **reduce** the width of the PMOS device!
 - ❑ widening the PMOS degrades the t_{pHL} due to larger parasitic capacitance

$$\beta = (W/L_p)/(W/L_n)$$

$r = R_{eqp}/R_{eqn}$ (resistance ratio of identically-sized PMOS and NMOS)

$$\beta_{opt} = \sqrt{r} \text{ when wiring capacitance is negligible}$$

PMOS/NMOS Ratio Effects



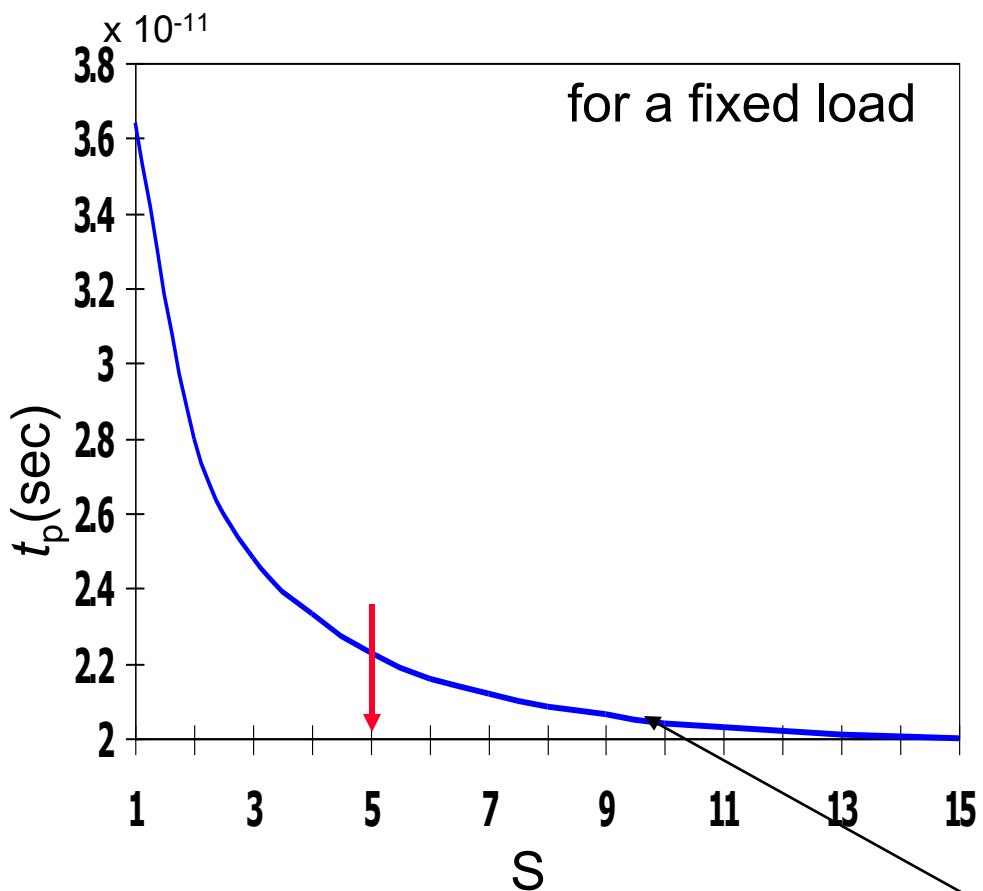
β of 2.4 ($= 31\text{ k}\Omega/13\text{ k}\Omega$) gives symmetrical response

β of 1.6 to 1.9 gives optimal performance

Device Sizing for Performance

- ❑ Divide capacitive load, C_L , into
 - C_{int} : intrinsic - diffusion and Miller effect
 - C_{ext} : extrinsic - wiring and fanout
- $t_p = 0.69 R_{eq} C_{int} (1 + C_{ext}/C_{int}) = t_{p0} (1 + C_{ext}/C_{int})$
- where $t_{p0} = 0.69 R_{eq} C_{int}$ is the intrinsic (**unloaded**) delay of the gate
- ❑ Widening both PMOS and NMOS by a factor **S** reduces R_{eq} by an identical factor ($R_{eq} = R_{ref}/S$), but raises the **intrinsic** capacitance by the same factor ($C_{int} = S C_{iref}$)
$$t_p = 0.69 R_{ref} C_{iref} (1 + C_{ext}/(S C_{iref})) = t_{p0}(1 + C_{ext}/(S C_{iref}))$$
 - t_{p0} is independent of the sizing of the gate; *with no load the drive of the gate is totally offset by the increased capacitance*
 - any S sufficiently larger than (C_{ext}/C_{int}) yields the best performance gains with least area impact

Sizing Impacts on Delay



The majority of the improvement is already obtained for $S = 5$. Sizing factors larger than 10 barely yield any extra gain (and cost significantly more area).

self-loading effect
(intrinsic capacitance
dominates)

Impact of Fanout on Delay

- ❑ Extrinsic capacitance, C_{ext} , is a function of the fanout of the gate - the larger the fanout, the larger the external load.
- ❑ First determine the **input loading** effect of the inverter. Both C_g and C_{int} are proportional to the gate sizing, so $C_{int} = \gamma C_g$ is independent of gate sizing and

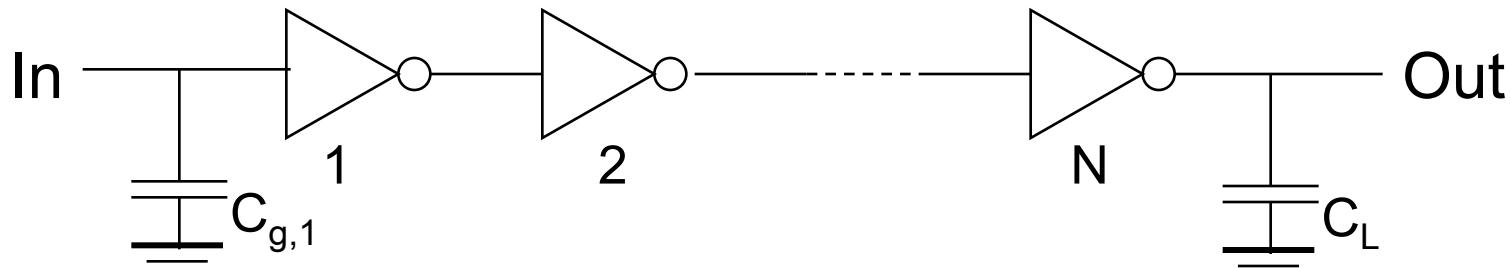
$$t_p = t_{p0} (1 + C_{ext} / \gamma C_g) = t_{p0} (1 + f/\gamma)$$

i.e., the delay of an inverter is a function of the ratio between its external load capacitance and its input gate capacitance: the **effective fan-out** f

$$f = C_{ext}/C_g$$

Inverter Chain

- Real goal is to minimize the delay through an inverter chain



the delay of the j-th inverter stage is

$$t_{p,j} = t_{p0} \left(1 + C_{g,j+1}/(\gamma C_{g,j})\right) = t_{p0}(1 + f_j/\gamma)$$

and $t_p = t_{p1} + t_{p2} + \dots + t_{pN}$

so $t_p = \sum t_{p,j} = t_{p0} \sum \left(1 + C_{g,j+1}/(\gamma C_{g,j})\right)$

- If C_L is given

- How should the inverters be sized?
- How many stages are needed to minimize the delay?

Sizing the Inverters in the Chain

- ❑ The optimum size of each inverter is the geometric mean of its neighbors – meaning that if each inverter is sized up by the same factor f wrt the preceding gate, it will have the same effective fan-out and the same delay

$$f = \sqrt[N]{C_L/C_{g,1}} = \sqrt[N]{F}$$

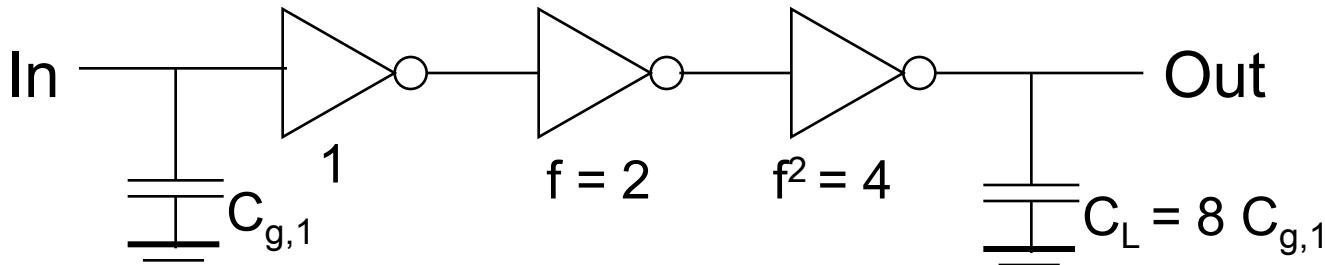
where F represents the overall effective fan-out of the circuit ($F = C_L/C_{g,1}$)

and the minimum delay through the inverter chain is

$$t_p = N t_{p0} \left(1 + \left(\sqrt[N]{F}\right) / \gamma\right)$$

- ❑ The relationship between t_p and F is linear for one inverter, square root for two, etc.

Example of Inverter Chain Sizing



- $C_L/C_{g,1}$ has to be evenly distributed over $N = 3$ inverters

$$C_L/C_{g,1} = 8/1$$

$$f = \sqrt[3]{8} = 2$$

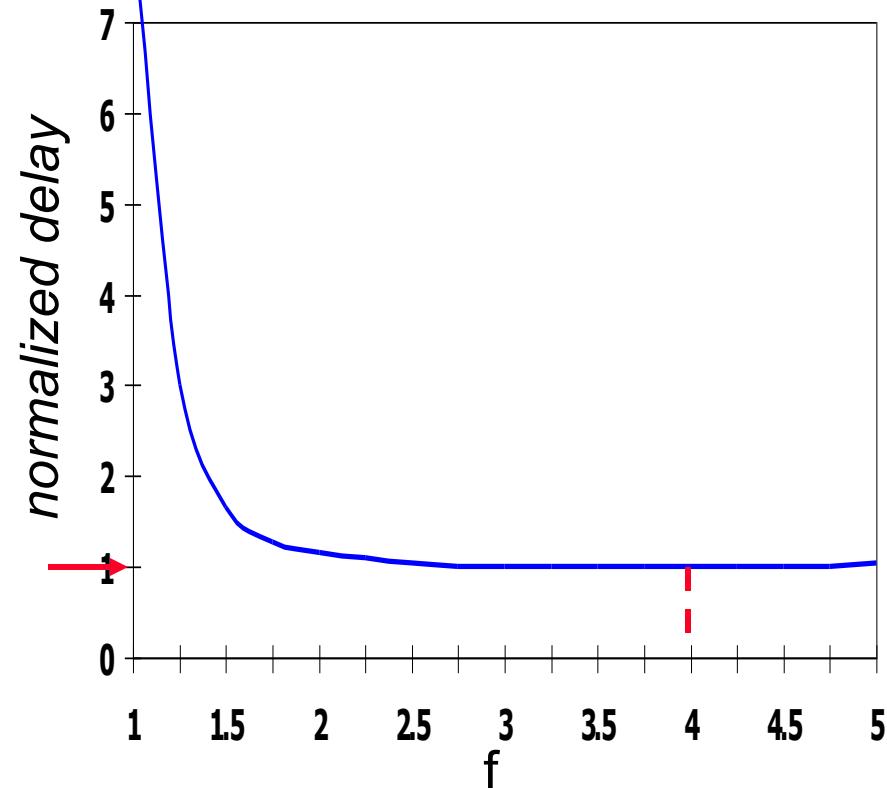
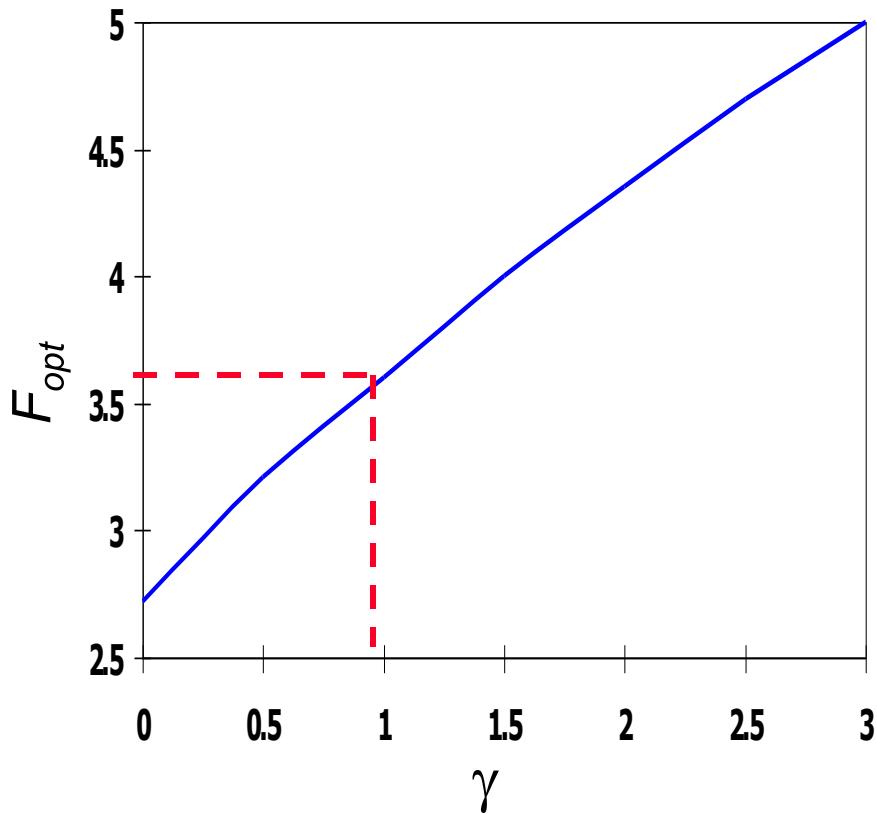
Determining N: Optimal Number of Inverters

- ❑ What is the optimal value for N given F ($=f^N$) ?
 - ❑ if the number of stages is too large, the intrinsic delay of the stages becomes dominate
 - ❑ if the number of stages is too small, the effective fan-out of each stage becomes dominate
- ❑ The optimum N is found by differentiating the minimum delay expression divided by the number of stages and setting the result to 0, giving

$$\gamma + \frac{N}{\sqrt[N]{F}} - \left(\frac{\sqrt[N]{F} \ln F}{N} \right) = 0$$

- ❑ For $\gamma = 0$ (ignoring self-loading) $N = \ln(F)$ and the effective-fan out becomes $f = e = 2.71828$
- ❑ For $\gamma = 1$ (the typical case) the optimum effective fan-out (tapering factor) turns out to be close to 3.6

Optimum Effective Fan-Out



- Choosing f larger than optimum has little effect on delay and reduces the number of stages (and area).
 - Common practice to use $f = 4$ (for $\gamma = 1$)
 - But **too many** stages has a substantial negative impact on delay

Example of Inverter (Buffer) Staging

N	f	t_p
1	64	65
2	8	18
3	4	15
4	2.8	15.3

Diagram illustrating the stages of inverter buffering:

- Stage 1: A single inverter with $C_{g,1} = 1$ driving a load $C_L = 64 C_{g,1}$.
- Stage 2: Two inverter stages in series. The first stage has $C_{g,1} = 1$ and the second stage has $C_{g,1} = 8$. The total load is $C_L = 64 C_{g,1}$.
- Stage 3: Three inverter stages in series. The first stage has $C_{g,1} = 1$, the second stage has $C_{g,1} = 4$, and the third stage has $C_{g,1} = 16$. The total load is $C_L = 64 C_{g,1}$.
- Stage 4: Four inverter stages in series. The first stage has $C_{g,1} = 1$, the second stage has $C_{g,1} = 2.8$, the third stage has $C_{g,1} = 8$, and the fourth stage has $C_{g,1} = 22.6$. The total load is $C_L = 64 C_{g,1}$.

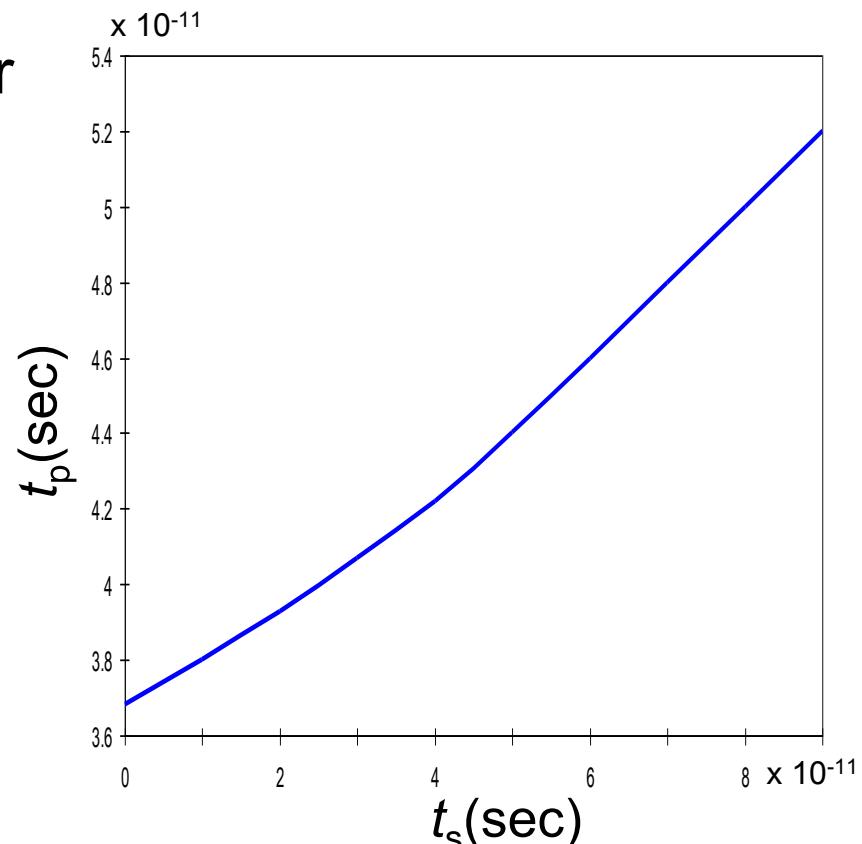
Impact of Buffer Staging for Large C

F ($\gamma = 1$)	Unbuffered	Two Stage Chain	Opt. Inverter Chain
10	11	8.3	8.3
100	101	22	16.5
1,000	1001	65	24.8
10,000	10,001	202	33.1

- ❑ Impressive speed-ups with optimized cascaded inverter chain for very large capacitive loads.

Input Signal Rise/Fall Time

- ❑ In reality, the **input** signal changes gradually (and both PMOS and NMOS conduct for a brief time). This affects the current available for charging/discharging C_L and impacts propagation delay.
- ❑ t_p increases **linearly** with increasing input slope, t_s , once $t_s > t_p$
- ❑ t_s is due to the limited driving capability of the preceding gate



for a minimum-size inverter
with a fan-out of a single gate

Design Challenge

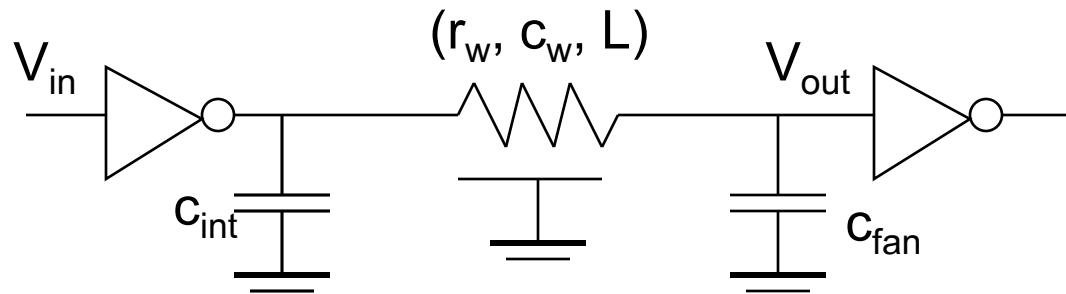
- ❑ A gate is never designed in isolation: its performance is affected by both the fan-out and the driving strength of the gate(s) feeding its inputs.

$$t_p^i = t_{\text{step}}^i + \eta t_{\text{step}}^{i-1} \quad (\eta \approx 0.25)$$

- ❑ Keep signal rise times smaller than or equal to the gate propagation delays.
 - ❑ good for performance
 - ❑ good for power consumption
- ❑ Keeping rise and fall times of the signals small and of approximately equal values is one of the major challenges in high-performance designs - **slope engineering**.

Delay with Long Interconnects

- When gates are farther apart, wire capacitance and resistance can no longer be ignored.



$$t_p = 0.69R_{dr}C_{int} + (0.69R_{dr} + 0.38R_w)C_w + 0.69(R_{dr} + R_w)C_{fan}$$

$$\text{where } R_{dr} = (R_{eqn} + R_{eqp})/2$$

$$= 0.69R_{dr}(C_{int} + C_{fan}) + 0.69(R_{dr}C_w + r_w C_{fan})L + 0.38r_w C_w L^2$$

- Wire delay rapidly becomes the dominate factor (due to the **quadratic term**) in the delay budget for longer wires.

Next Lecture and Reminders

❑ Next lecture

- Designing fast logic
 - Reading assignment – Rabaey, et al, 6.2.1

❑ Reminders

- Project specifications due today
- HW3 due next Thursday, Oct 10th (hand in to TA)
- Class cancelled on Oct 10th as make up for evening midterm
- I will be out of town Oct 10th through Oct 15th and Oct 18th through Oct 23rd, so office hours during those periods are cancelled
- We will have a guest lecturer on Oct 22nd
- Evening midterm exam scheduled
 - Wednesday, October 16th from 8:15 to 10:15pm in 260 Willard
 - Only one midterm conflict filed for so far